# MOSFET – Power, Single, P-Channel, TSOP-6 -20 V, -4.2 A

## **Features**

- Low R<sub>DS(on)</sub> in TSOP-6 Package
- 2.5 V Gate Rating
- Fast Switching
- This is a Pb-Free Device

# **Applications**

- Optimized for Battery and Load Management Applications in Portable Equipment
- Li Ion Battery Linear Mode Charging
- High Side Load Switch
- HDD Switching Circuits, Camera Phone, etc.

# MAXIMUM RATINGS (T<sub>J</sub> = 25°C unless otherwise stated)

Paran	Symbol	Value	Unit			
Drain-to-Source Voltage			$V_{DSS}$	-20	V	
Gate-to-Source Voltage	9		$V_{GS}$	±12	V	
Continuous Drain	Steady	T <sub>A</sub> = 25°C	I <sub>D</sub>	-3.7		
Current (Note 1)	State	T <sub>A</sub> = 85°C	]	-2.7	Α	
	t ≤ 5 s	T <sub>A</sub> = 25°C	]	-4.2		
Power Dissipation (Note 1)	Steady State		$P_D$	1.25		
(Note 1)	State	T <sub>A</sub> = 25°C			W	
	t ≤ 5 s			1.6		
Continuous Drain		T <sub>A</sub> = 25°C	I <sub>D</sub>	-2.7	Α	
Current (Note 2)	Steady	T <sub>A</sub> = 85°C	1	-2.0	A	
Power Dissipation (Note 2)	State	T <sub>A</sub> = 25°C	P <sub>D</sub>	0.7	W	
Pulsed Drain Current	t <sub>p</sub> = 10 μ	s	I <sub>DM</sub>	-15	Α	
Operating Junction and Storage Temperature			T <sub>J</sub> , T <sub>STG</sub>	–55 to 150	°C	
Lead Temperature for S (1/8" from case for 10 s)	TL	260	°C			

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

- Surface-mounted on FR4 board using 1 in sq pad size. (Cu area = 1.127 in sq [2 oz] including traces)
- Surface-mounted on FR4 board using the minimum recommended pad size. (Cu area = 0.0775 in sq)

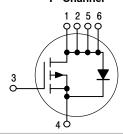


# ON Semiconductor®

## http://onsemi.com

V <sub>(BR)DSS</sub> R <sub>DS(ON)</sub> MAX		I <sub>D</sub> MAX
-20 V	60 mΩ @ -4.5 V	-3.7 A
	90 mΩ @ -2.7 V	-3.1 A
	100 mΩ @ -2.5 V	-3.0 A

# P-Channel



# MARKING DIAGRAM



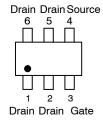
TSOP-6 CASE 318G STYLE 1



SB = Device Code
M = Date Code
Pb-Free Package

(Note: Microdot may be in either location)

# **PIN ASSIGNMENT**



# **ORDERING INFORMATION**

Device	Package	Shipping <sup>†</sup>
NTGS3443BT1G	TSOP-6 (Pb-Free)	3000 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

# THERMAL RESISTANCE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Junction-to-Ambient - Steady State (Note 3)	$R_{ hetaJA}$	100	
Junction-to-Ambient - t ≤ 5 s (Note 3)	$R_{ hetaJA}$	80	°C/W
Junction-to-Ambient - Steady State (Note 4)	$R_{ hetaJA}$	190	

<sup>3.</sup> Surface-mounted on FR4 board using 1 in sq pad size (Cu area = 1.127 in sq [2 oz] including traces).
4. Surface-mounted on FR4 board using the minimum recommended pad size (Cu area = 0.0775 in sq).

# **ELECTRICAL CHARACTERISTICS** ( $T_J = 25^{\circ}C$ unless otherwise specified)

Davamatas	Councile of	Total Comment	141	NA:	T	Mass	L laste
Parameter	Symbol	Test Condition		Min	Тур	Max	Unit
OFF CHARACTERISTICS							
Drain-to-Source Breakdown Voltage	V <sub>(BR)DSS</sub>	$V_{GS} = 0 \text{ V}, I_D = -250 \mu\text{A}$		-20			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V <sub>(BR)DSS</sub> /T <sub>J</sub>	I <sub>D</sub> = -250 μA, Reference 25°C			-15		mV/°C
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>GS</sub> = 0 V,	T <sub>J</sub> = 25°C			-1.0	μΑ
		$V_{DS} = -20 \text{ V}$	$V_{GS} = 0 \text{ V},$ $V_{DS} = -20 \text{ V}$ $T_{J} = 25^{\circ}\text{C}$ $T_{J} = 70^{\circ}\text{C}$			-5.0	1
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>DS</sub> = 0 V, V <sub>GS</sub>	= ±12 V			±0.1	μΑ
ON CHARACTERISTICS (Note 5)							
Gate Threshold Voltage	V <sub>GS(TH)</sub>	$V_{GS} = V_{DS}, I_D =$	-250 μA	-0.6		-1.4	٧
Negative Threshold Temperature Coefficient	V <sub>GS(TH)</sub> /T <sub>J</sub>				3.3		mV/°C
Drain-to-Source On Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> = -4.5 V, I <sub>D</sub>	<sub>0</sub> = -3.7 A		45	60	mΩ
	, ,	$V_{GS} = -2.7 \text{ V}, I_{D}$	<sub>0</sub> = -3.1 A		65	90	
		V <sub>GS</sub> = -2.5 V, I <sub>D</sub> = -3.0 A			70	100	
Forward Transconductance	9 <sub>FS</sub>	$V_{DS} = -10 \text{ V}, I_D = -3.7 \text{ A}$			7.0		S
CHARGES, CAPACITANCES AND GATE RES	ISTANCE			•			•
Input Capacitance	C <sub>ISS</sub>	$V_{GS} = 0 \text{ V, f} = 1 \text{ MHz, V}_{DS} = -10 \text{ V}$			819		pF
Output Capacitance	C <sub>OSS</sub>				157		1
Reverse Transfer Capacitance	C <sub>RSS</sub>				103		
Total Gate Charge	Q <sub>G(TOT)</sub>	$V_{GS} = -4.5 \text{ V}, V_{DS} = -10 \text{ V};$ $I_{D} = -3.7 \text{ A}$			8.0	11	nC
Threshold Gate Charge	Q <sub>G(TH)</sub>				0.6		1
Gate-to-Source Charge	Q <sub>GS</sub>	$I_D = -3.7$	Ä		1.7		<u></u>
Gate-to-Drain Charge	$Q_{GD}$				2.4		
Gate Resistance	R <sub>G</sub>				11		Ω
SWITCHING CHARACTERISTICS (Note 6)	•						•
Turn-On Delay Time	t <sub>d(ON)</sub>				10	15	ns
Rise Time	t <sub>r</sub>	$V_{GS} = -4.5 \text{ V}, V_{DD} = -10 \text{ V},$ $I_{D} = -1.0 \text{ A}, R_{G} = 6.0 \Omega$			7.0	11	
Turn-Off Delay Time	t <sub>d(OFF)</sub>				47	70	1
Fall Time	t <sub>f</sub>				25	40	1
DRAIN-SOURCE DIODE CHARACTERISTICS	;			-		-	-
Forward Diode Voltage	V <sub>SD</sub>	$V_{GS} = 0 \text{ V},$ $I_{J} = 25^{\circ}\text{C}$ $I_{S} = -1.7 \text{ A}$			-0.8	-1.2	V
Reverse Recovery Time	t <sub>RR</sub>	$V_{GS} = 0 \text{ V, } d_{IS}/d_t = 100 \text{ A/}\mu\text{s,}$ $I_S = -1.7 \text{ A}$			15	30	ns

<sup>5.</sup> Pulse Test: pulse width ≤ 300 μs, duty cycle ≤ 2%
6. Switching characteristics are independent of operating junction temperatures

# TYPICAL PERFORMANCE CURVES (T<sub>J</sub> = 25°C unless otherwise noted)

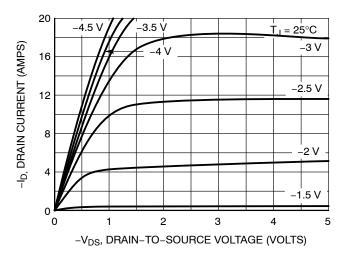


Figure 1. On-Region Characteristics

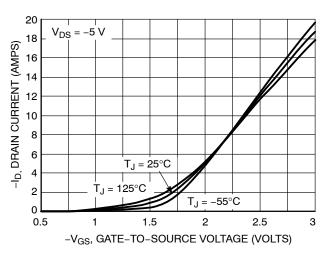


Figure 2. Transfer Characteristics

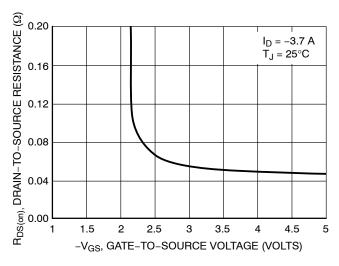


Figure 3. On-Resistance vs. Gate-to-Source Voltage

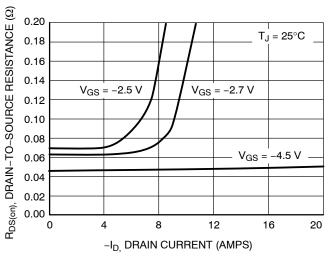


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

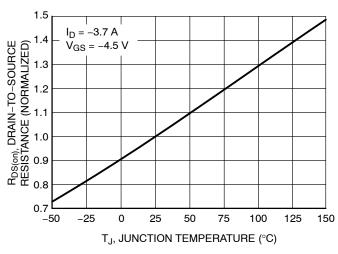


Figure 5. On–Resistance Variation with Temperature

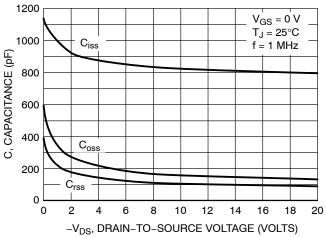


Figure 6. Capacitance Variation

# TYPICAL PERFORMANCE CURVES (T<sub>J</sub> = 25°C unless otherwise noted)

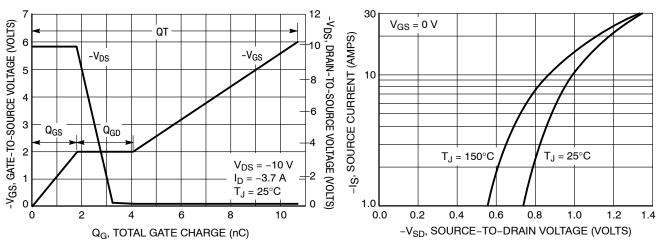


Figure 7. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

Figure 8. Diode Forward Voltage vs. Current

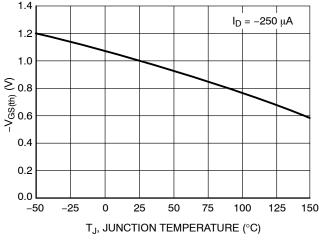


Figure 9. Threshold Voltage

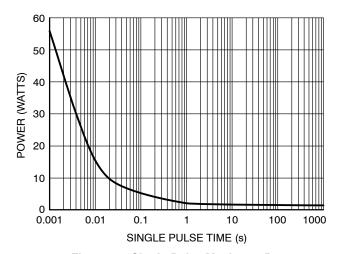


Figure 10. Single Pulse Maximum Power Dissipation

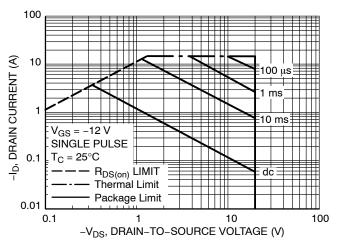


Figure 11. Maximum Rated Forward Biased Safe Operating Area

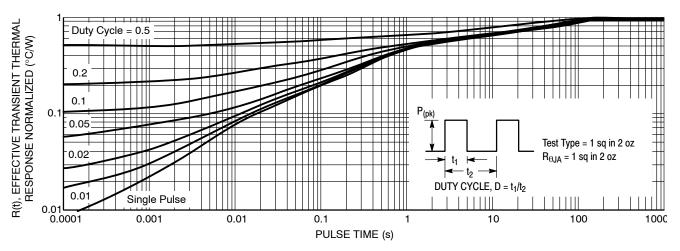


Figure 12. FET Thermal Response

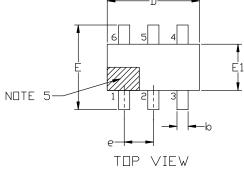


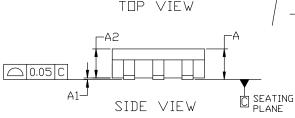


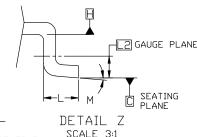
# TSOP-6 3.00x1.50x0.90, 0.95P **CASE 318G ISSUE W**

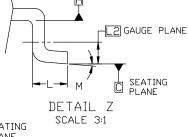
**DATE 26 FEB 2024** 

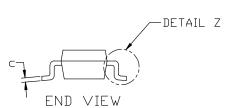










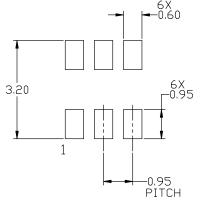


### NOTES

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2018.
- CONTROLLING DIMENSION: MILLIMETERS.
  MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM
  LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- 4. DIMENSIONS D AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.15 PER SIDE. DIMENSIONS D AND E1 ARE DETERMINED AT DATUM H.

  5. PIN 1 INDICATOR MUST BE LOCATED IN THE INDICATED ZONE

MILLIMETERS				
DIM	MIN	NDM	MAX	
А	0.90	1.00	1.10	
A1	0.01	0.06	0.10	
A2	0.80	0.90	1.00	
b	0.25	0.38	0.50	
U	0.10	0.18	0,26	
D	2.90	3.00	3.10	
E	2.50	2.75	3.00	
E1	1.30	1.50	1.70	
е	0.85	0.95	1,05	
Ĺ	0.20	0.40	0.60	
L2	0.25 BSC			
М	0°		10°	



# RECOMMENDED MOUNTING FOOTPRINT

\*For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference manual, SDLDERRM/D.

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DESCRIPTION:	TSOP-6 3.00x1.50x0.90, 0.	95P	PAGE 1 OF 2

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# TSOP-6 3.00x1.50x0.90, 0.95P CASE 318G ISSUE W

**DATE 26 FEB 2024** 

# GENERIC MARKING DIAGRAM\*



XXX M=

0 =

1 | | |

XXX = Specific Device Code XXX = Specific Device Code

A =Assembly Location M = Date Code
Y = Year ■ = Pb-Free Package

W = Work Week
■ Pb-Free Package

\*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLE 1: PIN 1. DRAIN 2. DRAIN 3. GATE 4. SOURCE 5. DRAIN 6. DRAIN	STYLE 2: PIN 1. EMITTER 2 2. BASE 1 3. COLLECTOR 1 4. EMITTER 1 5. BASE 2 6. COLLECTOR 2	STYLE 3: PIN 1. ENABLE 2. N/C 3. R BOOST 4. Vz 5. V in 6. V out	STYLE 4: PIN 1. N/C 2. V in 3. NOT USED 4. GROUND 5. ENABLE 6. LOAD	STYLE 5: PIN 1. EMITTER 2 2. BASE 2 3. COLLECTOR 1 4. EMITTER 1 5. BASE 1 6. COLLECTOR 2	STYLE 6: PIN 1. COLLECTOR 2. COLLECTOR 3. BASE 4. EMITTER 5. COLLECTOR 6. COLLECTOR
STYLE 7: PIN 1. COLLECTOR 2. COLLECTOR 3. BASE 4. N/C 5. COLLECTOR 6. EMITTER	STYLE 8: PIN 1. Vbus 2. D(in) 3. D(in)+ 4. D(out)+ 5. D(out) 6. GND	STYLE 9: PIN 1. LOW VOLTAGE GATE 2. DRAIN 3. SOURCE 4. DRAIN 5. DRAIN 6. HIGH VOLTAGE GATE	STYLE 10: PIN 1. D(OUT)+ 2. GND 3. D(OUT)- 4. D(IN)- 5. VBUS 6. D(IN)+	STYLE 11: PIN 1. SOURCE 1 2. DRAIN 2 3. DRAIN 2 4. SOURCE 2 5. GATE 1 6. DRAIN 1/GATE 2	STYLE 12: PIN 1. I/O 2. GROUND 3. I/O 4. I/O 5. VCC 6. I/O
STYLE 13: PIN 1. GATE 1 2. SOURCE 2 3. GATE 2 4. DRAIN 2 5. SOURCE 1 6. DRAIN 1	STYLE 14: PIN 1. ANODE 2. SOURCE 3. GATE 4. CATHODE/DRAIN 5. CATHODE/DRAIN 6. CATHODE/DRAIN	PIN 1. ANODE PIN 2. SOURCE 3. GATE 4. DRAIN 5. N/C	LE 16: 1. ANODE/CATHODE 2. BASE 3. EMITTER 4. COLLECTOR 5. ANODE 6. CATHODE	STYLE 17: PIN 1. EMITTER 2. BASE 3. ANODE/CATHODE 4. ANODE 5. CATHODE 6. COLLECTOR	

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